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T-31-15

PNP Silicon Planar Transistor

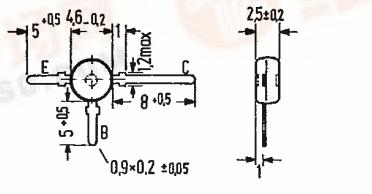
BF 967

SIEMENS AKTIENGESELLSCHAFT

for input stages up to 900 MHz

BF 967 is a PNP silicon UHF planar transistor with passivated surface in a low-capacitance plastic package similar to TO 119 (50 B 3 DIN 41867). The transistor is particularly suitable for use in low noise, gain-controlled input stages up to 900 MHz in tuners with diode tuning.

Type	Ordering code
BF 967	Q62702-F503



Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	30	V
Emitter-base voltage	$-V_{EBO}$	3	V
Collector current	$-I_C$	20	mA
Base current	$-I_B$	5	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Total power dissipation	P_{tot}	160	mW

Thermal resistance

Junction to ambient air	R_{thJA}	600	K/W
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SIEMENS AKTIENGESELLSCHAFT 5C 04579

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Static characteristics ($T_{amb} = 25^\circ\text{C}$)

Collector cutoff current

($-V_{CBO} = 15 \text{ V}$) $-I_{CBO}$ | 1 (<100)

nA

DC current gain

($-V_{CE} = 10 \text{ V}; -I_C = 1 \text{ mA}$) h_{FE} | 60 (>15)

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Emitter cutoff current

($-I_C = 0; -V_{EB} = 1 \text{ V}$) $-I_{EBO}$ | <100

nA

Dynamic characteristics ($T_{amb} = 25^\circ\text{C}$)

Transition frequency

($-I_C = 3 \text{ mA}; -V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$) f_T | 950

MHz

Reverse transfer capacitance

($-V_{CE} = 1 \text{ V}; f = 1 \text{ MHz}$) C_{12b} | 80

fF

Collector-base capacitance

($-V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$) $-C_{CBO}$ | 0.42

pF

Power gain

($-I_C = 3 \text{ mA}; -V_{CB} = 10 \text{ V}; f = 800 \text{ MHz};$ $R_L = 500 \Omega$) G_{pb} | 13

dB

Noise figure

($-I_C = 3 \text{ mA}; -V_{CB} = 10 \text{ V}; f = 800 \text{ MHz};$ $R_g = 60 \Omega$)

NF | 4

dB